

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| S1 | 2 | ("field oxide" near "active area") and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 11:12 |
| S2 | 0 | ("field oxide" near active) and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/22 11:39 |
| S3 | 0 | (oxide near active) and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/22 11:39 |
| S4 | 53 | oxide and active and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/22 13:27 |
| S5 | 0 | "CMOS image sensor" and "spacer insulation layer" and nitride and oxide and angstrom | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/22 13:29 |
| S6 | 51 | "CMOS image sensor" and spacer and nitride and oxide and angstrom | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/22 13:29 |
| S7 | 157 | "CMOS image sensor" and spacer and nitride and oxide and (angstrom near nitride or oxide) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/22 13:30 |
| S8 | 374 | "CMOS image sensor" and space and (angstrom near nitride or oxide) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/22 13:30 |

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| S9 | 56 | "CMOS image sensor" and (spacer near insulat\$4) and (angstrom near nitride or oxide) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/22 13:31 |
| S10 | 85 | "CMOS image sensor" and (spacer near4 insulat\$4) and (angstrom near4 nitride or oxide) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/22 13:30 |
| S11 | 219 | oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 11:17 |
| S12 | 198 | oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 11:18 |
| S13 | 186 | oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 11:18 |
| S14 | 110 | oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 11:18 |
| S15 | 110 | oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom and n-type and p-type | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 11:19 |

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| S16 | 108 | oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom and n-type and p-type and implant\$4 and mask | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 11:19 |
| S17 | 35 | oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom and n-type and p-type and implant\$4 and mask and photoresist | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 11:20 |
| S18 | 23 | oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom and n-type and p-type and implant\$4 and mask and photoresist and float\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/14 11:20 |